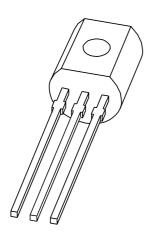
DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS5140S40 V low V_{CEsat} PNP transistor

Product specification

2001 Nov 15





40 V low V_{CEsat} PNP transistor

PBSS5140S

FEATURES

- High power dissipation (830 mW)
- · Ultra low collector-emitter saturation voltage
- 1 A continuous current
- · High current switching
- Improved device reliability due to reduced heat generation.

APPLICATIONS

- · Medium power switching and muting
- Linear regulators
- DC/DC converter
- · LCD back-lighting
- · Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT54 plastic package. NPN complement: PBSS4140S.

MARKING

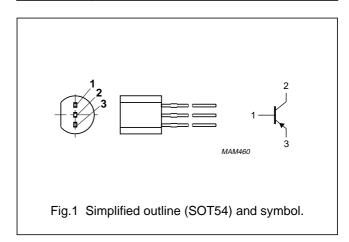
TYPE NUMBER	MARKING CODE
PBSS5140S	S5140S

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-40	V
I _C	collector current (DC)	-1	Α
I _{CM}	peak collector current	-2	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-40	V
V _{CEO}	collector-emitter voltage	open base	_	-40	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
Ic	collector current (DC)		_	-1	Α
I _{CM}	peak collector current		_	-2	Α
I _{BM}	peak base current		_	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	830	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	150	K/W

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

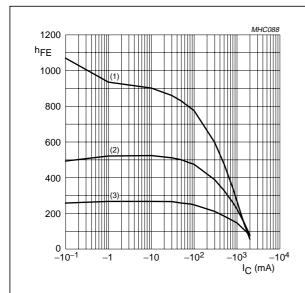
SYMBOL	PARAMETER	PARAMETER CONDITIONS		TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off	$V_{CB} = -40 \text{ V}; I_{C} = 0$	_	_	-100	nA
	current	$V_{CB} = -40 \text{ V}; I_{C} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0$	_	_	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ mA}$	300	_	_	
		$V_{CE} = -5 \text{ V}; I_{C} = -100 \text{ mA}$	300	_	800	
		$V_{CE} = -5 \text{ V}; I_{C} = -500 \text{ mA}$	250	_	_	
		$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}$	160	_	_	
V _{CEsat}	collector-emitter saturation	$I_C = -100 \text{ mA}; I_B = -1 \text{ mA}$	_	_	-200	mV
	voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	_	-250	mV
		$I_C = -1 \text{ A}; I_B = -100 \text{ mA}$	-	_	-500	mV
R _{CEsat}	equivalent on-resistance	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{ note 1}$	_	300	<500	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = -1 \text{ A}; I_B = -50 \text{ mA}$	_	_	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}$	_	_	-1	V
f _T	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 100 MHz	150	_	_	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	12	pF

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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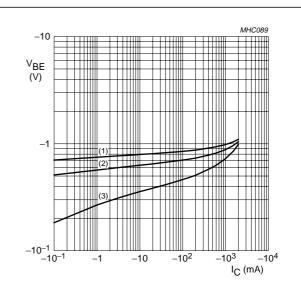
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 $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

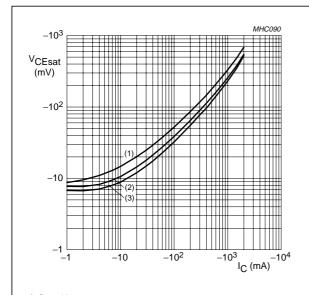
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = -55 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

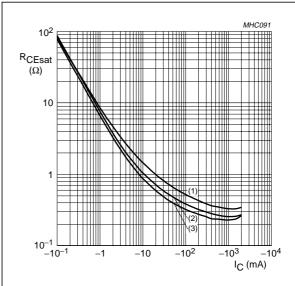
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \,^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

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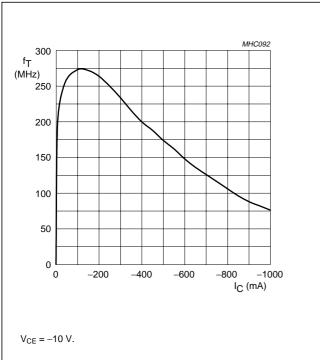


Fig.6 Transition frequency as a function of collector current.

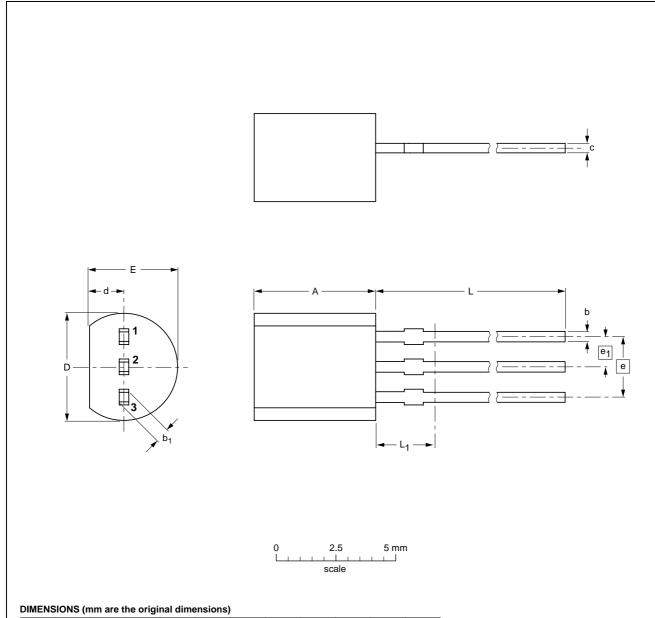
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE I	
SOT54		TO-92	SC-43			97-02-28

40 V low V_{CEsat} PNP transistor

PBSS5140S

DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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